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# P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
- 60	0.107 at V <sub>GS</sub> = - 10 V	- 30 <sup>d</sup>			
- 60	0.130 at V <sub>GS</sub> = - 4.5 V	- 20 <sup>d</sup>			

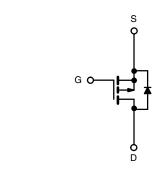
## **FEATURES**

- DT-Trench Power MOSFET
- Material categorization:

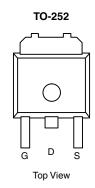


## **APPLICATIONS**

Load Switch



P-Channel MOSFET



ABSOLUTE MAXIMUM RATINGS (T	$_{\rm A}$ = 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V <sub>DS</sub>	- 60	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	v		
Continuous Drain Current (T <sub>.I</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	- 30 <sup>d</sup>		
Continuous Diam Current (1) = 175 C)	T <sub>C</sub> = 125 °C	I <sub>D</sub>	- 18	A	
Pulsed Drain Current	I <sub>DM</sub>	- 90	A		
Avalanche Current	I <sub>AS</sub>	- 25			
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	106	mJ	
Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	121 <sup>c</sup>	W	
rower dissipation	T <sub>A</sub> = 25 °C	'	2.7 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>b</sup>	t ≤ 10 s	- R <sub>thJA</sub>	12	15	°C/W	
Junction-to-Ambient	Steady State		35	45		
Junction-to-Case		$R_{thJC}$	0.8	1.1		

### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



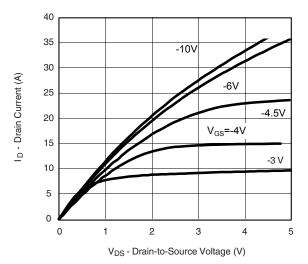
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•			•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			· v	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V			- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	μΑ	
		V <sub>DS</sub> = - 48 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 100	1	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 50			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		0.107	0.119		
D : 0	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 125 °C			0.131	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 150 °C			0.155		
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.130	0.145		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 10A		11		S	
Dynamic <sup>b</sup>	•				•		
Input Capacitance	C <sub>iss</sub>			1563			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		210		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Total Gate Charge <sup>c</sup>	$Q_g$			20	28		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$		11		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	]		13			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			10			
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -30 \text{ V}, R_{L} = 0.6 \Omega$		13			
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 40 A, $V_{GEN}$ = - 10 V, $R_G$ = 6 $\Omega$		35		ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	]		15			
Source-Drain Diode Ratings and Cha	aracteristics -	T <sub>C</sub> = 25 °C <sup>b</sup>			,		
Continuous Current	I <sub>S</sub>				- 30	۸	
Pulsed Current	I <sub>SM</sub>				- 60	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 30 A, V <sub>GS</sub> = 0 V		- 1	- 1.6	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 30 A, dI/dt = 100 A/μs		25	33	ns	

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

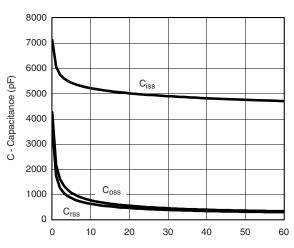
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



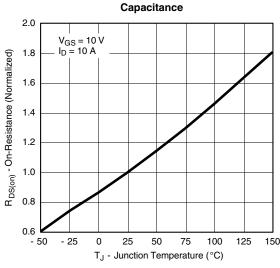
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



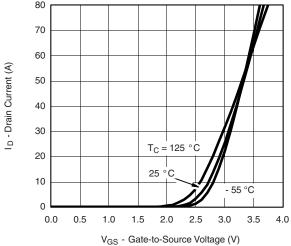
### **Output Characteristics**

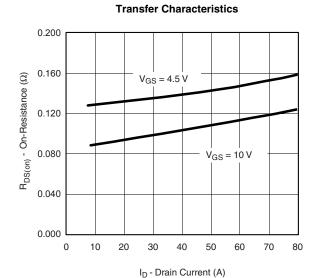


 $V_{DS}$  - Drain-to-Source Voltage (V)

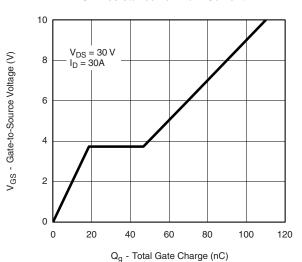


On-Resistance vs. Junction Temperature



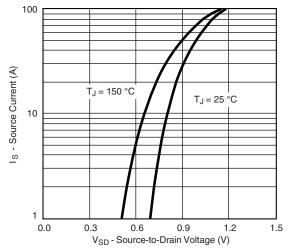


On-Resistance vs. Drain Current

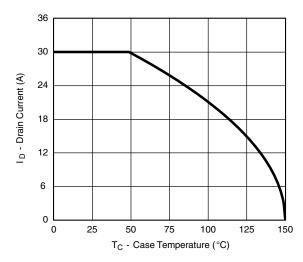


**Gate Charge** 

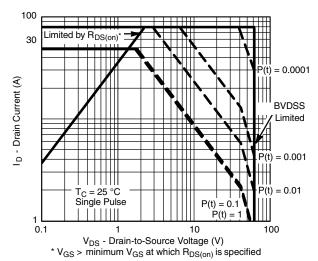
### **TYPICAL CHARACTERISTICS**



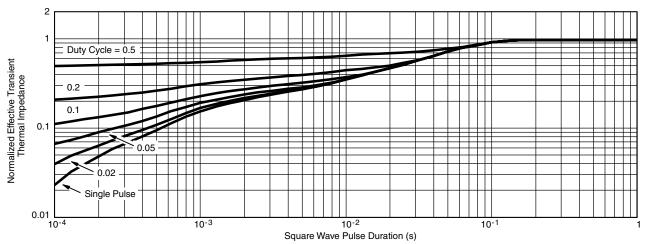
Source-Drain Diode Forward Voltage



**Drain Current vs. Case Temperature** 



**Safe Operating Area** 

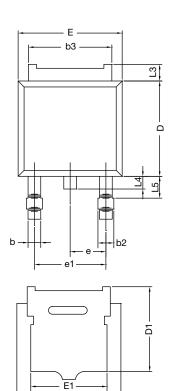


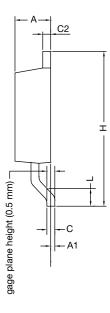
Normalized Thermal Transient Impedance, Junction-to-Case





# **TO-252AA CASE OUTLINE**





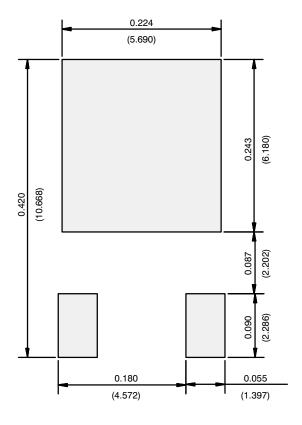
	MILLIN	METERS	INCHES			
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	5.21	-	0.205	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	2.28 BSC 0.090 E		BSC		
e1	4.56	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.14	1.52	0.045	0.060		
ECN: X12-0247-Rev. M, 24-Dec-12						

# DWG: 5347 Note

• Dimension L3 is for reference only.



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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